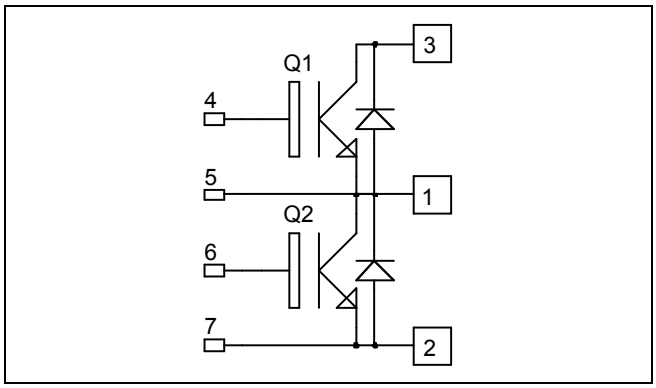
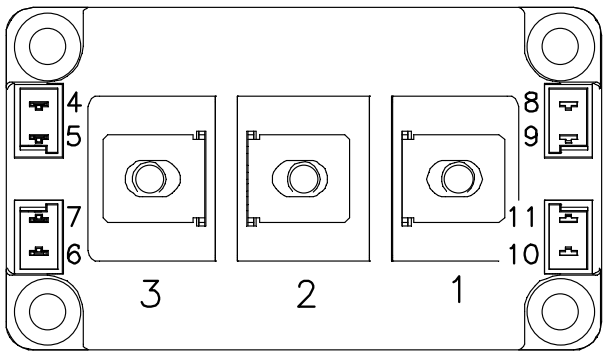
APTGT200A120D3G

Phase leg
Trench + Field Stop IGBT3
Power Module

V_{CES} = 1200V
I_C = 200A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	300	A
		T_C = 80°C	200	
I_{CM}	Pulsed Collector Current	T_C = 25°C	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	1050	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	400A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				500	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V I_C = 200A	T_j = 25°C	1.4	1.7	2.1	V
			T_j = 125°C		2.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 8mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V,V_{CE} = 25V f = 1MHz			14		nF
C_{rss}	Reverse Transfer Capacitance				0.6		
Q_G	Gate charge	V_{GE}=±15V, I_C=200A V_{CE}=600V			1.9		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.6Ω			250		ns
T_r	Rise Time				90		
$T_{d(off)}$	Turn-off Delay Time				550		
T_f	Fall Time				130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.6Ω			300		ns
T_r	Rise Time				100		
$T_{d(off)}$	Turn-off Delay Time				650		
T_f	Fall Time				180		
E_{on}	Turn on Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.6Ω	T_j = 125°C		15		mJ
E_{off}	Turn off Energy		T_j = 125°C		35		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p ≤ 10µs ; T_j = 125°C			800		A

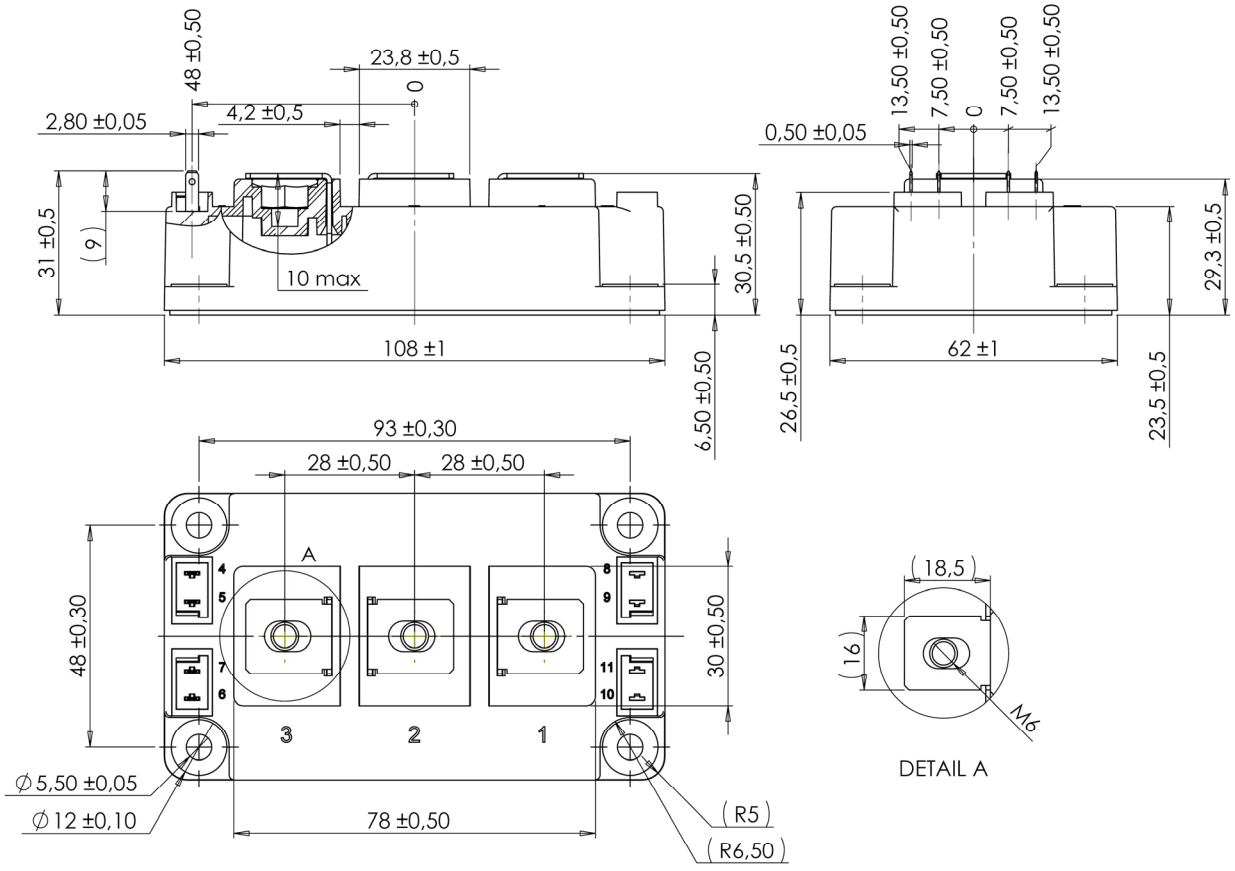
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C			750	µA
			T_j = 125°C			1000	
I_F	DC Forward Current		Tc = 80°C		200		A
V_F	Diode Forward Voltage	I_F = 200A V_{GE} = 0V	T_j = 25°C		1.6	2.1	V
			T_j = 125°C		1.6		
t_{rr}	Reverse Recovery Time	I_F = 200A V_R = 600V di/dt =3500A/µs	T_j = 25°C		170		ns
			T_j = 125°C		280		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		22		µC
			T_j = 125°C		40		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		9		mJ
			T_j = 125°C		16		

Thermal and package characteristics

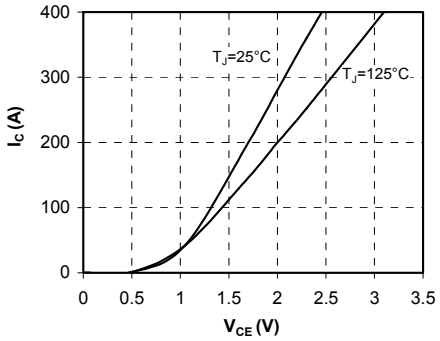
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.12	°C/W
			Diode			0.20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)

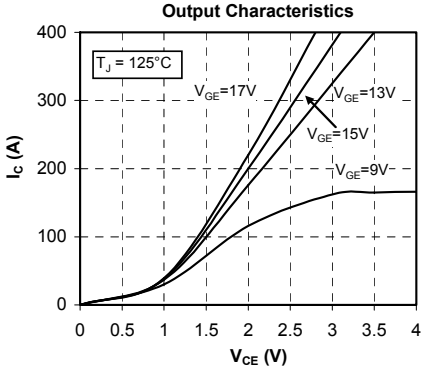


Typical Performance Curve

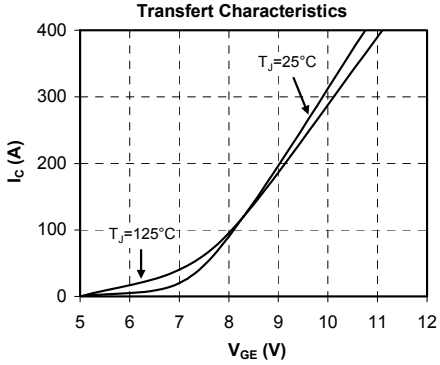
Output Characteristics (V_{GE}=15V)



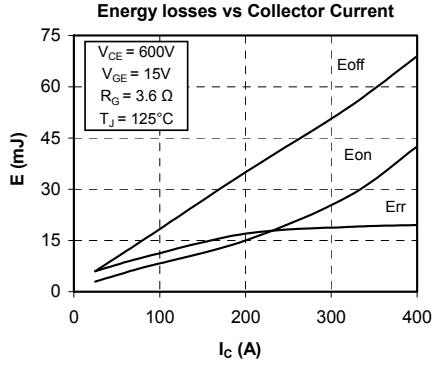
Output Characteristics



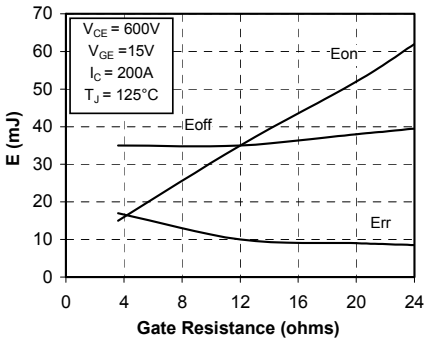
Transfert Characteristics



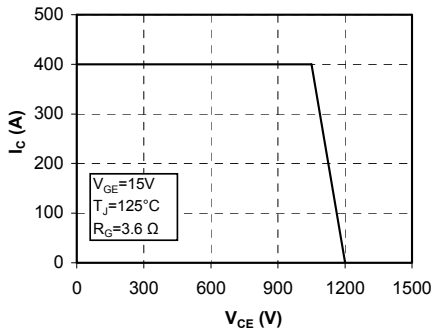
Energy losses vs Collector Current



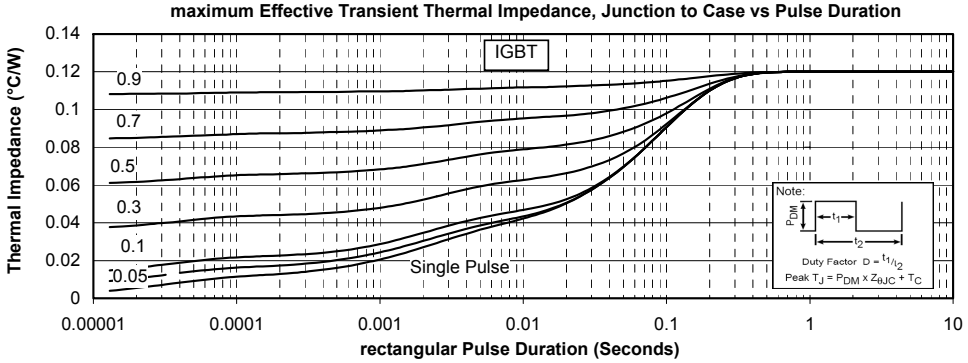
Switching Energy Losses vs Gate Resistance

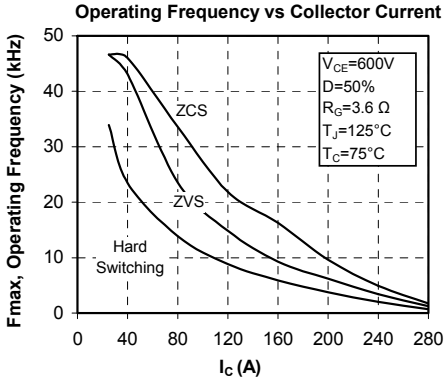


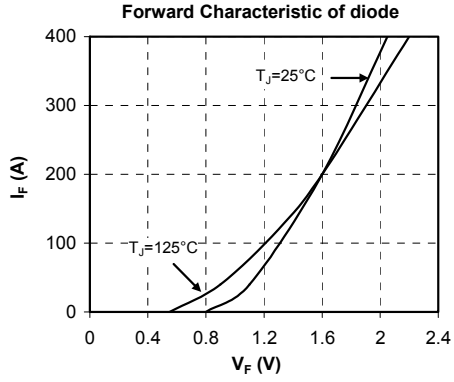
Reverse Bias Safe Operating Area

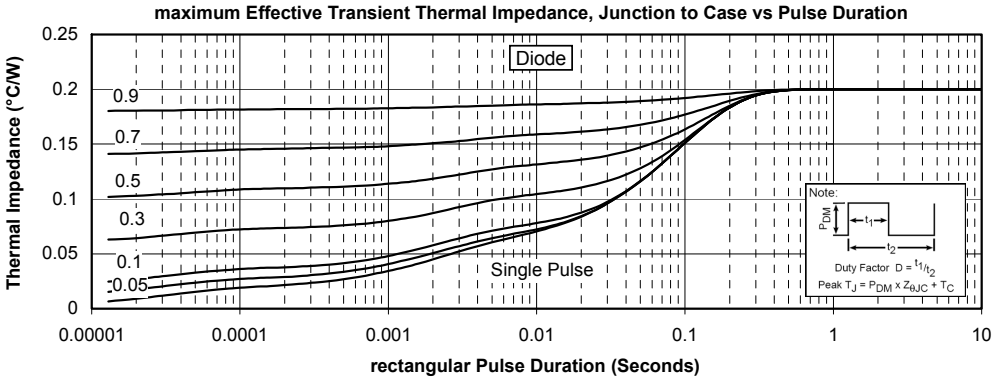


maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration









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